

Tm:KY_{1-x-y}Gd_xLu_y(WO₄)₂ planar waveguide laser passively Q-switched by single-walled carbon nanotubes

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Abstract: A Tm³⁺ monoclinic double tungstate planar waveguide laser is passively Q-switched (PQS) by a saturable absorber (SA) based on single-walled carbon nanotubes (SWCNTs) randomly oriented in a polymer film. The laser is based on a 18 μm-thick 5 at.% Tm:KY_{1-x-y}Gd_xLu_y(WO₄)₂ active layer grown on an undoped (010)-oriented KY(WO₄)₂ substrate by liquid phase epitaxy with determined propagation losses 0.7 ± 0.2 dB/cm. The PQS laser generated a maximum average output power of 45.6 mW at 1.8354 μm with a slope efficiency of 22.5%. Stable 83-ns-long laser pulses with an energy of 33 nJ were achieved at a repetition rate of 1.39 MHz. The use of SWCNTs as SA is promising for generation of sub-100 ns pulses in such waveguide lasers at ~2 μm.

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1. Introduction

Single-walled carbon nanotubes (SWCNTs) representing rolled sheets of graphene are emerging as broadband saturable absorbers (SAs) for passively Q-switched (PQS) and mode-locked lasers at 1–2 μm [1,2]. They exhibit relatively low saturation intensity, ultrafast recovery time of the initial absorption, high fraction of saturable loss and acceptable laser damage threshold [1–3]. Recently, SWCNT-SAs have been employed in compact 2- μm PQS bulk lasers based on Tm^{3+} or Ho^{3+} active ions, generating sub-100 ns pulses at high repetition rates approaching the MHz-range [3,4]. The performance of SWCNT-SAs in such lasers has proved to be superior to graphene-SAs and commercial semiconductor SAs [5].

Waveguide lasers emitting at $\sim 2 \mu\text{m}$ are of interest for environmental and medical sensing applications. To date, multiple studies focused on continuous-wave (CW) planar and channel Tm-doped waveguide lasers [6–9] including such featuring very high laser efficiency [10]. Only few reports on passive Q-switching of such waveguide lasers can be found [11–14], mostly due to the lack of suitable SAs in the 2- μm spectral range. The required SAs should exhibit low insertion losses, high modulation depth and low saturation intensity. In the present paper, we report on the successful application of SWCNT-SAs in a PQS planar waveguide laser based on a Tm^{3+} -doped monoclinic double tungstate (MDT) epitaxial structure, $\text{Tm:KY}_{1-x-y}\text{Gd}_x\text{Lu}_y(\text{WO}_4)_2$ / $\text{KY}(\text{WO}_4)_2$. Tm^{3+} -doped MDTs are known for their excellent spectroscopic properties [15], a prerequisite for high laser efficiency in waveguide lasers [10].

2. Experimental

The active layer with a composition $\text{KY}_{0.61}\text{Gd}_{0.22}\text{Lu}_{0.12}\text{Tm}_{0.05}(\text{WO}_4)_2$ (abbreviated: 5 at. % Tm:KYW, Tm^{3+} concentration: $N_{\text{Tm}} = 2.9 \times 10^{20} \text{ cm}^{-3}$) was grown by the liquid phase epitaxy (LPE) method on a (010)-oriented bulk substrate of an undoped $\text{KY}(\text{WO}_4)_2$ (KYW) crystal. A "mixed" active layer (i.e., incorporating Y^{3+} , Gd^{3+} and Lu^{3+} "passive"

ions) was used in order to reach simultaneously good lattice matching and high refractive index contrast with respect to the substrate [16,17]. The bulk crystal used as a substrate was grown by the Top-Seeded Solution Growth (TSSG) Slow-Cooling method using a [010]-oriented seed [15]. In both cases, potassium ditungstate, $K_2W_2O_7$, was used as a solvent. The solute/solvent ratio was 12/88 mol% and 7/93 mol% for the growth of the substrate and the epitaxial layer, respectively. The saturation temperature for the active layer T_S was 1160.7 K. During the LPE growth processes, ~ 8.0 mm of the substrate was vertically dipped into the solution while being rotated at 10 rev/min. The growth process took 3 hours at 3 K below T_S . Subsequently, the epitaxial layer was polished down to 18 μm thickness, Fig. 1(a). The sample was prepared for light propagation along the N_y optical indicatrix axis of the biaxial KYW. The refractive index contrast between the epitaxial layer and the substrate was estimated at the laser wavelength of ~ 1.84 μm using the Sellmeier equations [16] as $\Delta n \sim 0.004$ (for light polarization $E \parallel N_m$). The two end facets of the epitaxial structure were polished to laser quality, resulting in a final waveguide length l of 5.0 mm.

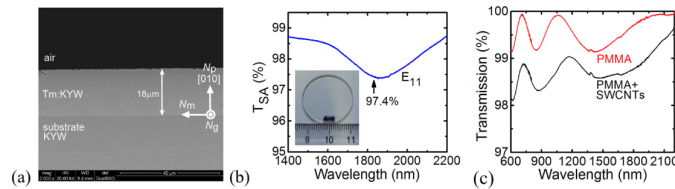


Fig. 1. (a) Environmental-SEM back-scattering image of the polished end-facet of the Tm:KYW/KYW epitaxy; (b) initial small-signal transmission of the SWCNT-SA (Fresnel losses are subtracted), *inset* – image of the SA. *Arrow* denotes the laser wavelength (PQS laser); (c) small-signal transmission spectra of SWCNT/PMMA and pure PMMA films of the same thickness (~ 200 nm).

The SWCNTs were synthesized by the arc-discharge technique with diameters spanning from 1.3 up to 1.5 nm. The SWCNT/PMMA (polymethylmethacrylate) mixture was spin-coated onto an uncoated 1-mm thick quartz substrate, wherein the individual SWCNTs exhibited a random (spaghetti-like) orientation [1,4]. The thickness of the coated SWCNT/PMMA layer was ~ 300 nm. The internal small-signal transmission spectrum of the SA shows a broad absorption band spanning from 1.6 to 2.2 μm , which is related to the first fundamental electronic transition of semiconducting carbon nanotubes (E_{11}), Fig. 1(b). The small-signal transmission T_{SA} of the SA was 97.4% at 1.84 μm . The saturation intensity I_S of a similar SA was estimated in [3] as ~ 7 MW/cm² and the fraction of the saturable losses $\alpha'_s/\alpha' \sim 0.21$ (in the 2 μm spectral range) [3], so that the modulation depth of the utilized SA at the laser wavelength was $\sim 0.54\%$.

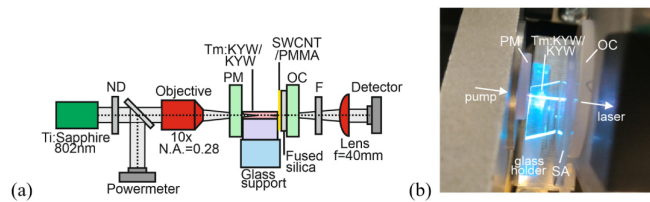


Fig. 2. (a) Scheme of the waveguide laser set-up: PM – pump mirror, OC – output coupler, ND – neutral density filter, F – long-pass filter; (b) blue upconversion luminescence from the PQS Tm:KYW planar waveguide laser.

To reveal the effect of PMMA on the linear absorption of the SA, we fabricated a similar SWCNT / PMMA film and an undoped PMMA film of the same thickness (~ 200 nm). Their small-signal transmission spectra are shown in Fig. 1(c). Both spectra contain similar interference-induced peaks and deeps while the transmission of the SWCNT / PMMA film is smaller. At a wavelength of 1.84 μm , the fraction of absorption due to the PMMA is minor (it is about 20%).

The scheme of the laser set-up is shown in Fig. 2(a). The Tm:KYW/KYW epitaxy was placed on a passively-cooled glass substrate. The laser cavity consisted of a flat pump mirror (PM) that was antireflection (AR) coated for 0.7–1 μm and high-reflection (HR) coated for 1.8–2.1 μm and a flat output coupler (OC) providing a transmission T_{OC} of 1.5%, 3%, 5%, 9%, 20% or 30% at 1.8–2.1 μm . A transmission-type SWCNT-SA was inserted between the waveguide and OC. All optical elements were placed as close as possible while avoiding the use of index-matching liquid. As pump source, a Ti:Sapphire laser tuned to 0.802 μm was used. A neutral density filter was applied to control the incident pump power. The polarization of the pump beam corresponded to $E \parallel N_m$ in the active layer. The pump was coupled into the waveguide by a $10 \times$ microscope objective lens (numerical aperture, N.A.: 0.28, focal length: $f = 20$ mm) resulting in a spot radius of 20 μm . About $48 \pm 3\%$ of the incident pump power was launched into the active layer, as determined from the pump-transmission measurements out of the Tm^{3+} absorption. ~ 86 –90% of the coupled light was absorbed under lasing conditions, as determined by a pump-transmission measurement under non-lasing conditions and rate-equation modelling. The unabsorbed residual pump was blocked with a long-pass filter (Thorlabs, FEL1000, transmission at the laser wavelength: $\sim 83\%$) and the output laser beam was collimated with an aspherical plano-convex lens ($f = 40$ mm). The spectrum of the laser emission was measured using a Yokogawa optical spectrum analyser (OSA, model AQ6375B) and the beam profile was captured with a FIND-R-SCOPE near-IR camera.

3. Results and discussion

At first, we studied the continuous-wave (CW) operation of the Tm:KYW waveguide laser, shown in Figs. 3(a) and 3(b). The maximum output power of 154 mW was achieved for $T_{\text{OC}} = 30\%$ at 1.8392 μm corresponding to a slope efficiency η of 52.2% (with respect to the absorbed pump power P_{abs}). The laser threshold was at $P_{\text{abs}} = 104$ mW. Increasing the output coupling from 1.5% to 30%, the emission wavelength decreased from 1.8467 to 1.8392 μm due to the quasi-three level nature of the Tm^{3+} laser, Fig. 3(b). The active layer emitted blue upconversion luminescence from the Tm^{3+} ions ($^1\text{G}_4 \rightarrow ^3\text{H}_6$ transition, centered at ~ 0.48 μm) as can be seen in Fig. 2(b). The propagation loss of the waveguide was estimated by applying the Caird analysis modified for high output coupling [18], $1/\eta = 1/\eta_0(1 + 2\gamma/\gamma_{\text{OC}})$, where $\gamma = -\ln(1 - L)$, L is the internal loss per pass, $\gamma_{\text{OC}} = -\ln(1 - T_{\text{OC}})$, and η_0 is the intrinsic slope efficiency. The Caird analysis is correct when the stimulated-emission cross-section is constant for the observed emission wavelengths. For Tm^{3+} ions in MDTs (for $E \parallel N_m$), its variation over 1.839–1.847 μm is minor [15]. From the linear fit shown in Fig. 3(c), values of $\eta_0 = 59\%$ and $L = 0.08 \pm 0.02$ are deduced, so that the propagation loss $\delta = 4.34L/l$ amounts to 0.7 ± 0.2 dB/cm. This indicates a high quality of the active layer.

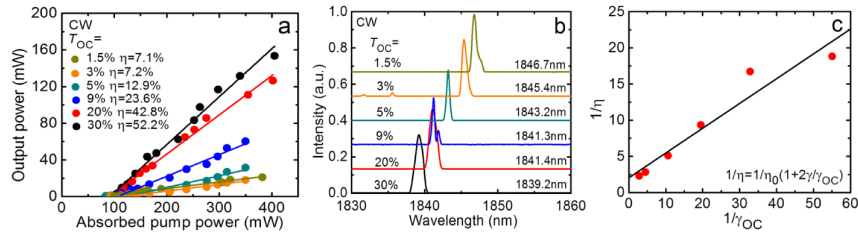


Fig. 3. CW Tm:KYW planar waveguide laser: (a) input-output dependences, η – slope efficiency; (b) typical laser emission spectra measured at maximum P_{abs} ; (c) Caird analysis modified for high output coupling. The laser polarization is $E \parallel N_m$.

In the PQS operation mode, depicted in Fig. 4, the laser generated a maximum average output power of 45.6 mW at 1.8354 μm with $\eta = 22.5\%$ (for $T_{\text{OC}} = 30\%$). The laser threshold was at $P_{\text{abs}} = 150$ mW and the conversion efficiency with respect to the CW operation mode η_{conv} was 29%. For lower $T_{\text{OC}} = 20\%$ and 9%, the laser slope efficiency was inferior: 16.3% and 8.3%, respectively. Further power scaling was limited by the available pump source. The emission wavelength slightly shortened with the

increase of T_{OC} , from 1.8371 to 1.8354 μm for the same reason as explained above for the CW regime, Fig. 4(b). The beam profile of the laser was slightly elliptic with a large extension in the non-guided plane of the waveguide, see inset of Fig. 4(a). According to the dispersion relation [19], the waveguide supports two transversal electric (TE) modes along the guided direction at a wavelength of $\sim 1.84 \mu\text{m}$. In both operation regimes, CW and PQS, the laser emission was linearly polarized, $E \parallel N_m$. The polarization was naturally-selected by the anisotropy of the gain.

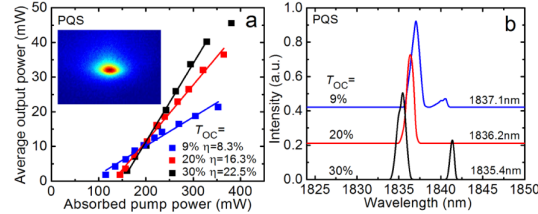


Fig. 4. SWCNT PQS Tm:KYW planar waveguide laser: (a) input-output dependences, η – slope efficiency; (b) typical laser emission spectra measured at maximum P_{abs} . The laser polarization is $E \parallel N_m$. Inset in (a) – far-field profile of the laser mode for $T_{OC} = 30\%$, $P_{abs} = 330 \text{ mW}$.

The pulse characteristics of the PQS Tm:KYW waveguide laser varied with P_{abs} . The pulse duration $\Delta\tau$ (determined as full width at half maximum, FWHM) decreased from 161 to 83 ns, the pulse energy E_{out} increased from 7.6 to 32.8 nJ and the pulse repetition frequency (PRF) increased almost linearly from 0.94 to 1.39 MHz when P_{abs} was increased from 176 to 381 mW (for $T_{OC} = 30\%$), see Fig. 5. Such a behavior is typical for PQS lasers containing “fast” SAs and is related to the variable bleaching of the SA [20]. The shortest pulse duration (71 ns) corresponded to $T_{OC} = 9\%$ due to the higher intracavity peak intensity at the SA ($\sim 1.5 \text{ MW/cm}^2$). However, $T_{OC} = 30\%$ provided a higher pulse energy and, thus, the maximum peak power $P_{peak} = E_{out}/\Delta\tau$ reached 395 mW.

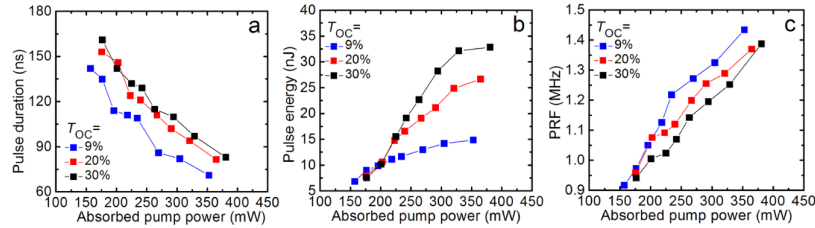


Fig. 5. SWCNT PQS Tm:KYW planar waveguide lasers: (a) pulse duration (FWHM), (b) pulse energy and (c) pulse repetition frequency (PRF) vs. absorbed pump power.

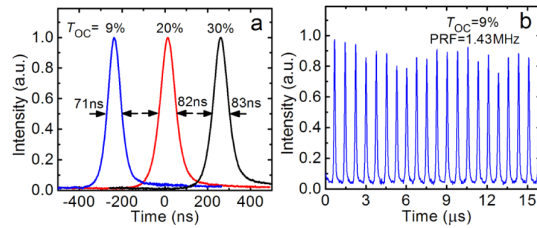


Fig. 6. Oscilloscope traces of the SWCNT PQS Tm:KYW planar waveguide laser output recorded by a fast InGaAs photodiode at maximum P_{abs} : (a) shortest single Q-switched pulses for the applied OCs; (b) corresponding pulse train for $T_{OC} = 9\%$.

The oscilloscope traces of the shortest single Q-switched pulses are shown in Fig. 6(a). The pulses exhibit a Gaussian temporal shape. The corresponding pulse train for $T_{OC} = 9\%$ measured at the maximum $P_{abs} = 352 \text{ mW}$ is shown in Fig. 6(b). The intensity fluctuations are $<20\%$ and they are mostly attributed to heating of the SA by non-

absorbed pump power [21]. During PQS operation, no damage of the SWCNT-SA was observed.

In the previous studies of PQS Tm-doped waveguide lasers [11–13,22], see details in Table 1, “slow” (e.g., polycrystalline $\text{Cr}^{2+}:\text{ZnSe}$) and “fast” SAs (e.g., graphene, Bi_2Te_3 topological insulator (TI)) were used. These lead to the generation of relatively long pulses, from tens of ns to few μs , as well as low output power. Recently, using a similar Tm:KYW/KYW epitaxy, we achieved 195 ns/5.8 nJ pulses (average output power: 6.5 mW) using a chemical vapor deposition grown graphene-SA [23]. Also, very recently, a SWCNT-SA was employed in a PQS fs-laser-written Tm:KLu(WO_4)₂ channel waveguide laser generating shorter pulses (50 ns/7 nJ) while the output power (10.3 mW) and the slope efficiency (3.8%) were relatively low most probably because of moderate waveguide propagation losses [14]. Thus, the present study presents a record in output characteristics for PQS Tm³⁺-doped waveguide lasers in terms of average output power and slope efficiency. This performance is attributed to the high fraction of the saturable losses for the SWCNT-SA as compared to graphene and TIs, as well as a relatively low saturation intensity of the SWCNT-SA [3].

Table 1. Output Characteristics of PQS Thulium Waveguide Lasers Reported So Far

Gain material	Geometry / fabrication*	SA	P_{out} , mW	η , %	$\Delta\tau$, ns	E_{out} , nJ	PRF, kHz	P_{peak} , mW	Ref.
Tm:ZBLAN	channel / fs	graphene	6	~5	2760	240	25	87	[12]
Tm:ZBLAN	channel / fs	Bi_2Te_3	16.3	1.3	1400	370	44.1	264	[22]
Tm:YAG	channel / fs	graphene	6.5	~2	<500	9.5	684	~20	[13]
Tm:KLuW	channel / fs	SWCNTs	10.3	3.8	50	7	1480	141	[14]
Tm:KYW	planar / LPE	graphene	6.5	9	195	5.8	1130	30	[23]
Tm:KYW	planar / LPE	$\text{Cr}^{2+}:\text{ZnS}$	1.2	~3	1200	120	10	100	[11]
Tm:KYW	planar / LPE	SWCNTs	45.6	22.5	83	33	1390	395	**

*fs – femtosecond direct laser writing; LPE – liquid phase epitaxy growth.

**This work.

4. Conclusion

SWCNT-SAs are very suitable for passive Q-switching of $\sim 2 \mu\text{m}$ waveguide lasers as demonstrated by PQS of a 18 μm -thick 5 at.% Tm:KY_{1-x-y}Gd_xLu_y(WO_4)₂/KY(WO_4)₂ epitaxy as active medium. The Tm³⁺-doped planar waveguide laser delivered sub-100 ns pulses (71–83 ns) at ~ 1 MHz repetition rates. The maximum average output power was ~ 46 mW, the slope efficiency 22.5% and the Q-switching conversion efficiency 29%. Further shortening of the laser pulses down to few tens of ns and power scaling are expected substituting the planar by a channel waveguide geometry and using butt-coupled laser mirrors. Deposition of the SWCNTs on top of the waveguide for evanescent field interaction might further reduce the losses in the cavity.

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